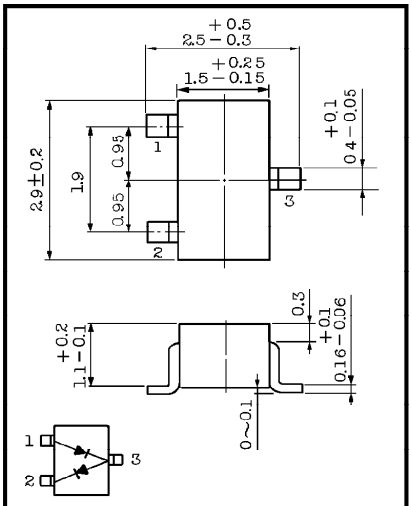
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS374

HIGH SPEED SWITCHING APPLICATION

Unit in mm



1. ANODE1
2. CATHODE2
3. CATHODE1, ANODE2

S-MINI

JEDEC	TO-236MOD
EIAJ	SC-59
TOSHIBA	1-3G1G

Weight : 0.012g

- Small Package
- Low Forward Voltage : $V_{F(2)}$ = 0.23V (TYP.) @I_F = 5mA

MAXIMUM RATINGS (Ta = 25°C)

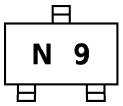
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200※	mA
Average Forward Current	I_O	100※	mA
Surge Current (10ms)	I_{FSM}	1※	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C
Operating Temperature Range	T_{opr}	−40~100	°C

※ Unit Rating. Total Rating = Unit Rating × 0.7

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

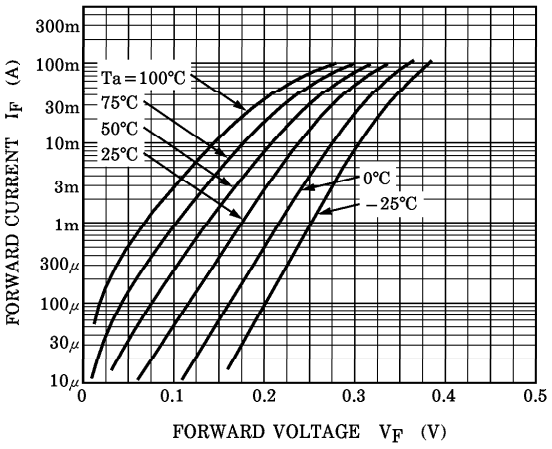
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F = 1mA	—	0.18	—	V
	$V_{F(2)}$	I_F = 5mA	—	0.23	0.30	
	$V_{F(3)}$	I_F = 100mA	—	0.35	0.50	
Reverse Current	I_R	V_R = 10V	—	—	20	μA
Total Capacitance	C_T	V_R = 0, f = 1MHz	—	20	40	pF

MARKING

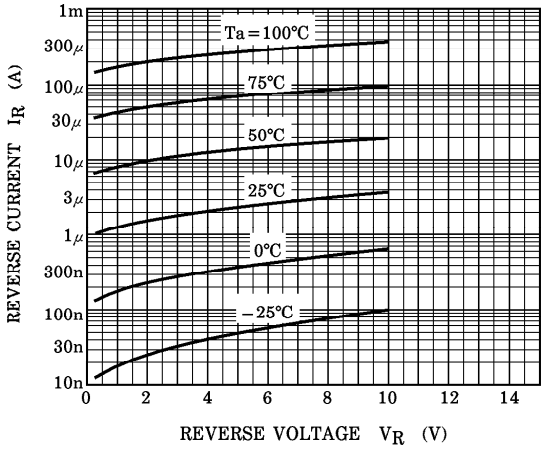


961001EAA2

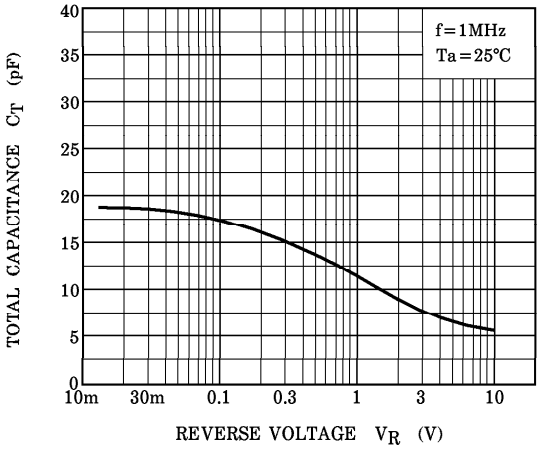
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



P – Ta